

# **PSMN013-100PS**

N-channel 100V 13.9mΩ standard level MOSFET in TO220.

10 August 2012 Product data sheet

# 1. Product profile

### 1.1 General description

Standard level N-channel MOSFET in TO220 package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- · Improved dynamic avalanche performance
- · Suitable for standard level gate drive

### 1.3 Applications

- DC-to-DC converters
- Load switching
- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	100	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	[1]	-	-	68	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	170	W
T <sub>j</sub>	junction temperature			-55	-	175	°C
Static characte	eristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 °C;$ Fig. 12		-	19.4	25	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ Fig. 13	[2]	-	10.8	13.9	mΩ
Dynamic chara	Dynamic characteristics						
$Q_{GD}$	gate-drain charge	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; Fig. 15; Fig. 14		-	17	-	nC



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q <sub>G(tot)</sub>	total gate charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; V_{DS} = 50 \text{ V};$ Fig. 14; Fig. 15	-	59	-	nC
Avalanche rug	gedness					
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 68 A; $V_{sup} \le$ 100 V; unclamped; $R_{GS}$ = 50 $\Omega$	-	-	128	mJ

- Continuous current is limited by package Measured 3 mm from package.

# **Pinning information**

**Pinning information** Table 2.

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain	1 7 9	
3	S	source		G 4
mb	D	mounting base; connected to drain		mbb076 S
			TO-220AB (SOT78)	

# **Ordering information**

Table 3. **Ordering information** 

Type number	Package	ackage				
	Name	Description	Version			
PSMN013-100PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

# **Marking**

Table 4. **Marking codes** 

Type number	Marking code
PSMN013-100PS	PSMN013-100PS

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	100	V
$V_{DGR}$	drain-gate voltage	$T_j \le 175$ °C; $T_j \ge 25$ °C; $R_{GS} = 20$ kΩ		-	100	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 1</u>	[1]	-	47	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	[1]	-	68	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 °C$ ; Fig. 3		-	272	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	170	W
T <sub>stg</sub>	storage temperature			-55	175	°C
T <sub>j</sub>	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-dra	in diode	'				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	68	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	272	Α
Avalanche	ruggedness			,		
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 68 A; $V_{sup}$ ≤ 100 V; unclamped; $R_{GS}$ = 50 Ω		-	128	mJ

<sup>[1]</sup> Continuous current is limited by package

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Nexperia PSMN013-100PS

#### N-channel 100V 13.9m $\Omega$ standard level MOSFET in TO220.

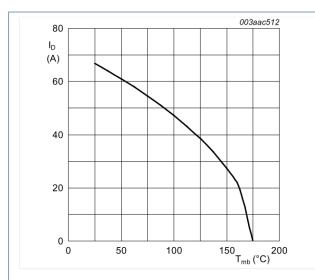


Fig. 1. Continuous drain current as a function of mounting base temperature

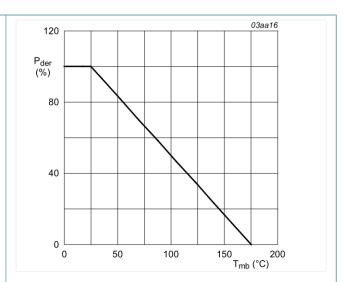


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

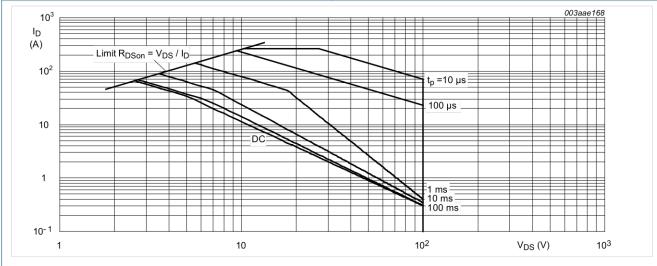


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb}$  = 25 °C;  $I_{DM}$  is a single pulse

## 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 4	-	0.5	0.9	K/W

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W

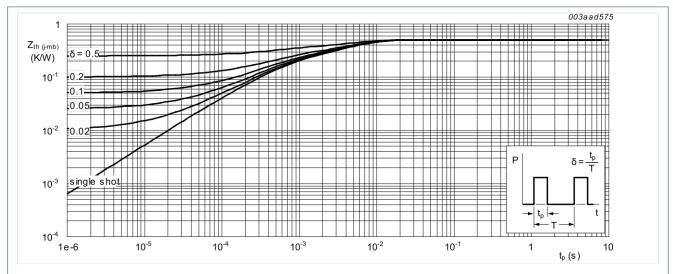


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

### 7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					'
(DIX)DOO	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 ^{\circ}\text{C}$	90	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	100	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 10	1	-	-	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; Fig. 10; Fig. 11	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	4.6	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	-	100	μA
		V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.06	2	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	10	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	10	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 100 °C; Fig. 12	-	19.4	25	mΩ

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 175 °C; Fig. 12		-	29.5	38.9	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; Fig. 13	[1]	-	10.8	13.9	mΩ
$R_G$	internal gate resistance (AC)	f = 1 MHz		-	1	-	Ω
Dynamic ch	naracteristics						
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V; Fig. 14; Fig. 15		-	59	-	nC
		I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 10 V		-	47.6	-	nC
$Q_{GS}$	gate-source charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V; Fig. 14; Fig. 15		-	13.8	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V; Fig. 15		-	9.2	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge			-	4.6	-	nC
$Q_{GD}$	gate-drain charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V; Fig. 15; Fig. 14		-	17	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	V <sub>DS</sub> = 50 V; <u>Fig. 15</u> ; <u>Fig. 14</u>		-	4.4	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 0 V; f = 1 MHz;		-	3195	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 16</u>		-	221	-	pF
C <sub>rss</sub>	reverse transfer capacitance			-	136	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 2 \Omega; V_{GS} = 10 \text{ V};$		-	20.7	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega; T_j = 25 °C$		-	25	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	52.5	-	ns
t <sub>f</sub>	fall time			-	24	-	ns
Source-dra	in diode				,		
V <sub>SD</sub>	source-drain voltage	$I_S = 15 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 17$		-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = 100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	52	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 50 V		-	109	-	nC

<sup>[1]</sup> Measured 3 mm from package.

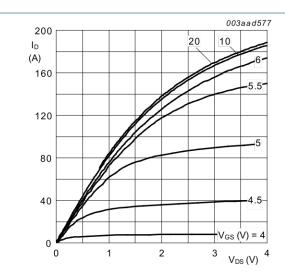


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values

$$T_j = 25 \,^{\circ}C$$

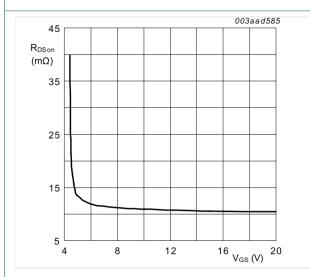


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25 \,^{\circ}C$$

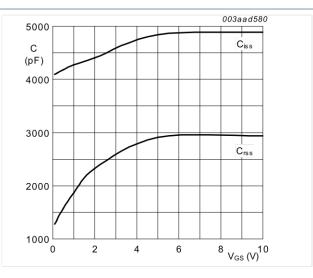


Fig. 6. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

$$V_{DS} = 0V; f = 1MHZ$$

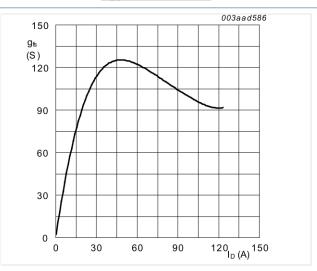


Fig. 8. Forward transconductance as a function of drain current; typical values

$$T_j = 25 \,{}^{\circ}C; V_{DS} = 15 \, V$$

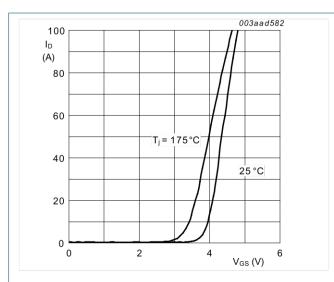


Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values



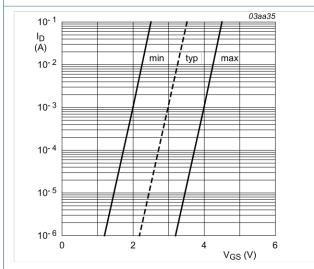


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

$$T_J = 25\,^{\circ}C; V_{DS} = 5V$$

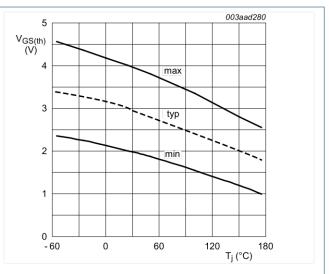


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}$$
;  $V_{DS} = V_{GS}$ 

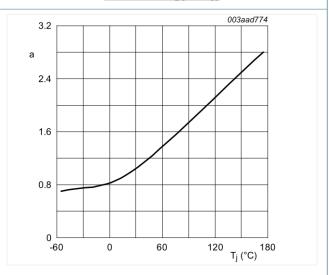


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$\mathbf{a} = \frac{R_{DSon}}{R_{DSon(25 \, ^{\circ}\text{C})}}$$

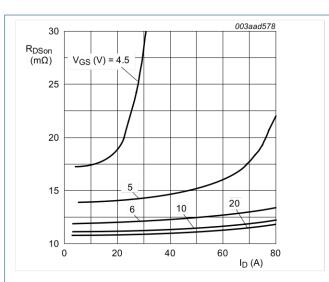


Fig. 13. Drain-source on-state resistance as a function of drain current; typical values

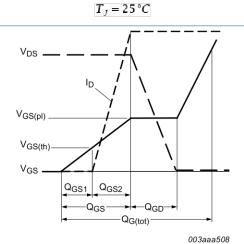


Fig. 15. Gate charge waveform definitions

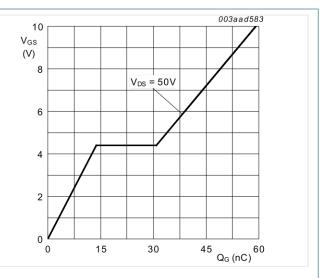


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_J = 25 \,^{\circ}C; I_D = 25A$$

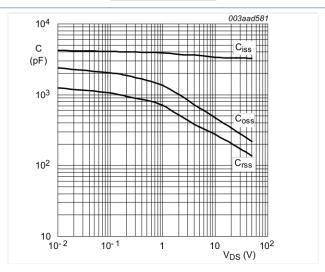


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$

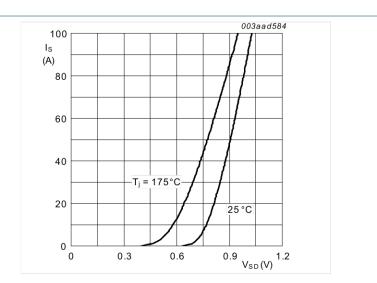
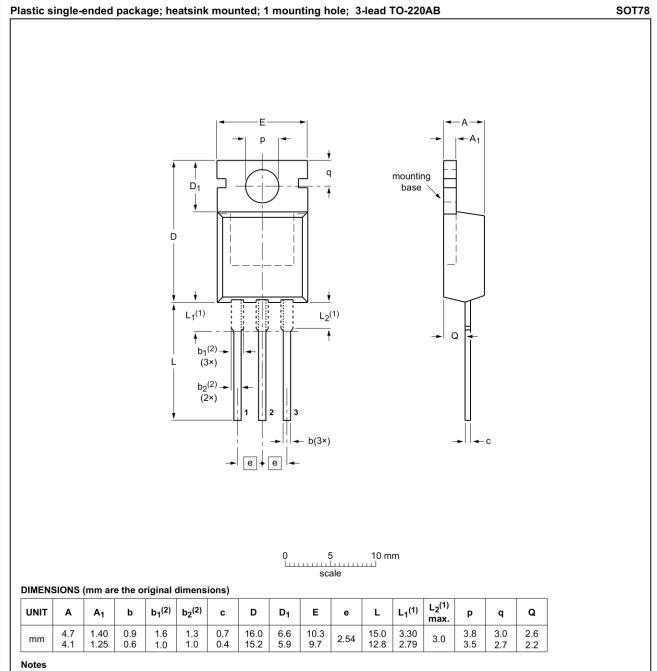


Fig. 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

# 8. Package outline



- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	REFERENCES			ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE
SOT78		3-lead TO-220AB	SC-46			<del>08-04-23</del> 08-06-13

Fig. 18. TO-220AB (SOT78)

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Document status [1][2]	Product status [3]	Definition
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